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# Dominating Factors on Dispersion of MC Interphase Precipitation in Low Carbon Steels

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#### Interphase precipitation



#### Precipitation strengthening



N. Kamikawa et al., *ISIJ Int.* 54 (2014) 212.

 Larger precipitation strengthening can be obtained by refining MC until nano size.



A.D. Batte et al., Met. Sci. J., 7 (1973) 160.

- Interfacial coherency
- Interfacial migration rate
- Interfacial supersaturation



- Density of defects ¬
- → Time
- $\rightarrow$  Driving force

for nucleation

Variations in dispersion of interphase precipitation

The effects of transformation temperature and alloying elements on the dispersion of interphase precipitation and resultant strengthening in low carbon steels were quantitatively studied mainly by using **three-dimensional atom probe**.

Based on this, **the dominating factors** on the dispersion of interphase precipitation will be further discussed.

#### **Experimental procedures**

- Alloys (mass%)

   Base:
   Fe-0.1C-1.5Mn-0.05Si (M-free)

   V-added:
   Fe-0.1C-1.5Mn-0.05Si-0.1V / 0.2V / 0.4V

   Fe-0.2C-1.5Mn-0.05Si-0.4V (High C)
   Fe-0.1C-0.7Mn-0.05Si-0.4V (Low Mn)

   Fe-0.1C-1.5Mn-0.05Si-0.4V (Low Mn)
   Fe-0.1C-1.5Mn-0.05Si-0.4V (High Si)

   Fe-0.1C-1.5Mn-0.05Si-0.4V (High Si)
   Fe-0.1C-1.5Mn-0.05Si-0.4V -150ppmN (High N)

   Nb-added:
   Fe-0.1C-1.5Mn-0.05Si-0.05Nb / 0.1Nb

   Ti-added:
   Fe-0.1C-1.5Mn-0.05Si-0.05Ti / 0.1Ti / 0.2Ti
- Heat treatment



- Microstructural characterization
  - Optical microscopy (OM)
  - Scanning electron microscopy (SEM) / Electron backscatter diffraction (EBSD)
  - Three-dimensional atom probe (3DAP)
- Property measurement
  - Vickers hardness measurement (9.8N / 0.25N)
  - Nanoindentation measurement (500µN)

#### Effects of temperature on microstructure and hardness



GBF: grain boundary  $\alpha$ ; WF: Widmanstatten  $\alpha$ ; BF: bainite  $\alpha$ ; IGF: intragranular  $\alpha$ ; M( $\gamma$ ): martensite

0.1C-0.4V

# VC precipitation in $\alpha$ with different $\alpha/\gamma$ orientation relationship



PAGB: prior  $\gamma$  grain boundary; M( $\gamma$ ): martensite; GBF: grain boundary  $\alpha$ ; WF: Widmanstatten  $\alpha$ ;

 $\Delta \theta$ : deviation angle from the exact Kurdjumov-Sachs orientation relationship (K-S OR) Three-dimensional V atom map

7

WF ( $\Delta \theta$  = 0.8deg.)



- $\alpha$  transformation is proceeded by the migration of both near K-S and non K-S  $\alpha/\gamma$  interface.
- Almost no VC precipitate exists in WF with near K-S OR, while VC interphase precipitation is observed in GBF with non K-S OR.



Y.-J. Zhang et al., Scr. Mater. 69 (2013) 17.

- As α/γ OR deviates from exact K-S, number density of VC increases significantly at first and remains almost constant later, while the size of VC is only slightly increased.
- Higher number density of VC in  $\alpha$  grains with non K-S OR results in higher nanohardness compared with those with near K-S OR.

## Segregation of V at non K-S $\alpha/\gamma$ interface



• In addition to C, V is also severely segregated at non K-S  $\alpha/\gamma$  interface.

## Effects of temperature on dispersion of VC and nanohardness 10



Y.-J. Zhang et al., *Acta Mater.* 84 (2015) 375.

- The dispersion of VC tends to be finer, i.e. higher in number density and smaller in size by lowering the transformation temperature.
- Finer dispersion increases nanohardness with similar volume fraction.

#### Effects of V content on dispersion of VC



 Number density of VC increases with higher V content, while variations in size of VC is relatively small.

#### Effects of C content on dispersion of VC



Although growth rate of α becomes significantly lower by increasing C content, dispersion of VC is almost unchanged.

# Alloying effects on microstructure and interphase precipitation 13

Non K-S

#### 0.1C-0.4V-based, 993K, 60s



- WF formation is promoted by lower Mn content, but almost unchanged with higher Si or higher N content.
- Dispersion of interphase precipitation is not largely changed by lower Mn, higher Si and N contents, although  $\alpha$  growth rate is quite different.



- Lower Mn, higher Si and higher N contents only slightly refine the dispersion of interphase precipitation.
- Finer dispersion of interphase precipitation gives higher nanohardness.

#### Estimation of interfacial concentration



• Compared with PE model, NPLE model gives better prediction of  $\alpha/\gamma$  phase equilibria in V-added low carbon steels.

# Composition of VC and driving force for its precipitation



By assuming 50at% V and 50at% C:

 $\Delta G = 0.5 \mu_V + 0.5 \mu_C - G_{VC}$  $\Delta G : \text{driving force};$  $\mu_i : \text{chemical potential of } i;$  $G_{VC} : \text{free energy}$ 

(Segregation is neglected for simplicity)



#### Effects of $\alpha$ growth rate and driving force for precipitation



 Compared with α growth rate, dispersion of interphase precipitation shows better correlations with driving force for its precipitation.

# Aging time and interfacial diffusion at migrating $\alpha/\gamma$ interface 18



#### Comparison of dispersion of MC and hardness



 With similar amount of addition, the dispersion of NbC and TiC is much finer than VC, resulting in higher hardness.



- Higher number density of NbC and TiC is also obtained by more addition, whose dispersion is much finer than VC.
- Although dispersion of NbC is slightly finer than TiC, their strengthening ability is similar but much stronger than VC.



- Consistently with VC, dispersion of NbC and TiC becomes finer by enlarging the driving force for precipitation.
- Larger driving force for precipitation is necessary to obtain similar number density of NbC and TiC as VC.

Additional free energy:

$$\Delta G_{v}^{G-T} = \frac{2\sigma}{r}$$

 $\sigma$  :  $\alpha$ /MC interfacial energy;

*r* : radius



 G-T effects cannot be neglected in the case of MC interphase precipitates with nano size.

## V content in $\alpha$ and remained driving force for precipitation



- Much higher content of V than its solubility still remains in α.
- More V and larger driving force remain with higher bulk content.
- Driving force is only slightly decreased after precipitation.

23

Ideal solution approximation: in  $\alpha$  $\Delta G = RT \ln \frac{X_C^{\alpha} \cdot X_V^{\alpha}}{X_C^S \cdot X_V^S} = RT \ln \frac{X_V^{\alpha}}{X_V^S}$ solubility

#### Relationship between initial and remained driving force



 Remained driving force is nearly proportional to initial one under various conditions.

bulk in 
$$\alpha$$
  
 $f \propto X_M^{ppt} = X_M - X_M^{\alpha}$   
 $= X_M \left( 1 - \exp\left(\frac{\Delta G^R - \Delta G^I}{RT}\right) \right)$ 



 Observed radius is inversely proportional to remained driving force under G-T effects with various interfacial energies.

$$r = rac{2\sigma}{\Delta G^R} \propto rac{2\sigma}{\Delta G^I}$$

$$\begin{split} \sigma_{\alpha/\text{VC}} &= 1.5\text{J/m}^2;\\ \sigma_{\alpha/\text{NbC}} &= 1.5\text{J/m}^2;\\ \sigma_{\alpha/\text{TiC}} &= 2.1\text{J/m}^2. \end{split}$$

#### Dominating factors on number density of MC



Number density is estimated as:

$$\rho \approx k X_M \frac{\Delta G_V^I}{\sigma^3}$$

*k* : constant;  $X_M$  : bulk M content;  $\Delta G_V'$  : initial driving force for MC precipitation;  $\sigma$  :  $\alpha$ /MC interfacial energy;



 Number density divided by bulk M content against driving force shows much smaller deviation, whereas the deviation between V, Nb and Ti can be explained by the difference in α/MC interfacial energy. The effects of various factors on dispersion of interphase precipitation as well as its resultant precipitation strengthening in low carbon steels were systematically investigated in this study. Based on all the experimental results, this study is summarized as:

- 1. Interphase precipitation behaviors strongly depend on  $\alpha/\gamma$  orientation relationship that large deviation from the exact K-S one promotes the formation of VC interphase precipitation.
- 2.  $\alpha$  growth rate only has minor influence on the dispersion of interphase precipitation.
- 3. Transformation temperature and alloying elements affect the dispersion of interphase precipitation mainly by changing the driving force for its precipitation.
- 4. Finer dispersion of interphase precipitation results in higher hardness of  $\alpha$  grains due to larger precipitation strengthening.

#### Combination of EBSD, 3DAP and nano-indentation

① EBSD  $\rightarrow \alpha$ -orientation map + 001bcc pole figure  $\rightarrow \alpha/\gamma$  OR analyses:



## $\alpha/\gamma$ crystallography and mechanisms of interphase precipitation29



R.A. Ricks et al., Acta Metall. 31 (1983) 853.

# Variations in dispersion with aging time at migrating interface 30





Fe-V binary

© ASM International 2006. Diagram No. 907267

M. P. Seah et al., Proc. Royal Society of London 335. (1973) 191.

 Alloying elements with lower solubility tend to be severely segregated at grain boundary. Fe-0.2C-2.0Mn-0.3V: Aging @1173K, 3.6ks

V map:

Fe-0.1C-1.5Mn-0.1V: α transformation @923K, 60s V map:



• V segregation occurs both at  $\gamma$  grain boundary and at  $\alpha/\gamma$  interface.



 $\theta$ : misorientation angle

K. Tatsumi, et al., *Trans. JIM* 27 (1986) 427.

B.W. Krakauer et al. Metal. Sci. Forum 126-128 (1993) 161.

 Larger misorientation results in severer segregation possibly due to lower coherency with larger free volume.



- Aging time at migrating  $\alpha/\gamma$  interface is reversely proportional to macroscopic  $\alpha$  growth rate.
- Similar dispersion of VC in alloys with different C contents indicates that aging time does not have large influence on interphase precipitation.

Ashby-Orowan model:

$$\Delta \tau = 0.84 \left(\frac{1.2Gb}{2\pi L}\right) \cdot \ln \frac{x}{2b}$$
$$x = 2\bar{r} \sqrt{\frac{2}{3}}$$

Hardness increment:

$$\Delta HV = HV_{M-added} - HV_{Pure Fe}$$
$$= HV_{ss} + HV_{disl} + HV_{ppt}$$

- *G* : shear modulus of  $\alpha$ ;
- *b* : Burgers vector of  $\alpha$ ;
- L : inter-particle spacing of MC on slip plane;
- x : average diameter of MC on slip plane;
- $\bar{r}$  : average radius of MC

T. Gladman, Mater. Sci. Tech. 15 (1999) 30.



 Higher hardness increment of α by precipitation strengthening can be obtained by reducing the inter-particle spacing of MC.



- Higher number density of NbC and TiC is also obtained by more addition, whose dispersion is much finer than VC.
- Volume fraction of NbC and TiC also tends to be higher than VC, whose strengthening ability is much stronger than VC.

With different driving force for precipitation:



- More V remains in  $\alpha$  in V-added alloys with higher bulk V content.
- Same phenomenon can also be observed in Nb and Ti-added alloys, although Nb and Ti contents in  $\alpha$  tend to be lower than V content.

With same driving force for precipitation:

$$(L = \sqrt{2D_V t} \quad \begin{array}{l} D_V : \text{ diffusivity of V} \\ \text{at interface / in } \alpha \end{array}$$



(Estimated from  $\alpha$  growth rate and inter-sheet spacing)

• Both the aging times at  $\alpha/\gamma$  interface and in  $\alpha$  are not enough for V content in  $\alpha$  to be decreased to its solubility.

#### Single variant of randomly dispersed VC precipitates









#### Promotion of VC nucleation at non K-S interface



Baker-Nutting (B-N) OR: (001)<sub> $\alpha$ </sub> // (001)<sub>VC</sub>, [110]<sub> $\alpha$ </sub> // [100]<sub>VC</sub>

	σ (J / m <sup>2</sup> )	Exp. / Calc.	Ref.
α/γ Κ-S	~0.3	Calc.	[1]
$\alpha/\gamma$ random	~0.8	Exp.	[2]
γ/VC semi-coh.	~1.9	Calc.	[3]
γ/VC incoh.	~2.6	Calc.	[3]
α/VC semi-coh.	~0.6	Calc.	[4]

$$\Delta \sigma \approx \sigma_{\alpha/VC} + \sigma_{\gamma/VC} - \sigma_{\alpha/\gamma}$$

 $= 2.2 \text{ J/m}^2$  Near K-S case

 $= 2.4 \text{ J/m}^2$  Non K-S case

 Promotion VC nucleation at non K-S interface is mainly caused by higher interfacial diffusivity and segregation of V, instead of higher α/γ interfacial energy.

[1] M. Enomoto et al., PTM (2005) 67.

- [2] L.E. Murr, Int. Phen. in Metals and Alloys (1975) 124.
- [3] T. Furuhara et al., ISIJ Int. 43 (2003) 1630.

[4] D.H.R. Fors et al., Phys. Rev. B. 82 (2010) 195410.

## Segregation of V at non K-S $\alpha/\gamma$ interface



• In addition to C, V is also severely segregated at non K-S  $\alpha/\gamma$  interface.